



256Kx32 Static RAM CMOS, High Speed Module

FEATURES

- 256Kx32 bit CMOS Static RAM
 - Access Times: 12, 15, 20, and 25ns
 - Individual Byte Selects
 - Fully Static, No Clocks
 - TTL Compatible I/O
- High Density Package with JEDEC Standard Pinouts
 - 72 Pin SIMM No. 175 (Angle)
 - 72 Pin ZIP No. 176
 - 72 Pin SIMM, No. 354 (Straight)
- Single +3.3V ($\pm 10\%$) Supply Operation

DESCRIPTION

The EDI8F32259V is a high speed 8Mb Static RAM module organized as 256K words by 32 bits. This module is constructed from eight 256Kx4 Static RAMs in SOJ packages on an epoxy laminate (FR4) board.

Four chip enables ($\overline{E0}$ - $\overline{E3}$) are used to independently enable the four bytes. Reading or writing can be executed on individual bytes or any combination of multiple bytes through proper use of selects.

The EDI8F32259V is offered in 72 pin ZIP/SIMM package which enables eight megabits of memory to be placed in less than 1.3 square inches of board space.

All inputs and outputs are TTL compatible and operate from a single 3.3V supply. Fully asynchronous circuitry requires no clocks or refreshing for operation and provides equal access and cycle times for ease of use.

The ZIP and SIMM modules contain four PD (Presence Detect) pins which are used to identify module memory density in applications where alternate modules can be interchanged.

FIG. 1

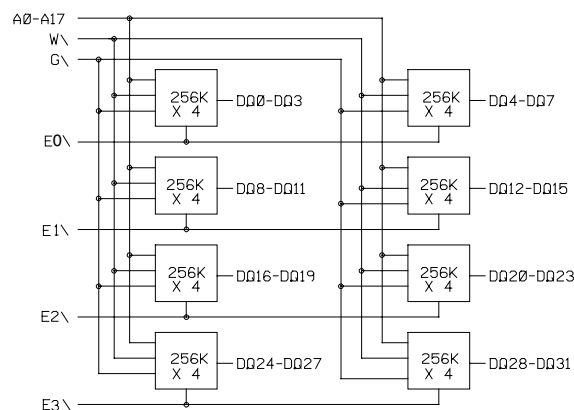
PIN CONFIGURATIONS AND BLOCK DIAGRAM

NC □1	E4 \ □37
NC □2	E3 \ □38
PD3 □3	A17 □39
PD4 □4	A16 □40
VSS □5	G \ □41
PD1 □6	VSS □42
PD2 □7	DQ24 □43
DQ0 □8	DQ16 □44
DQ8 □9	DQ25 □45
DQ1 □10	DQ17 □46
DQ9 □11	DQ26 □47
DQ2 □12	DQ18 □48
DQ10 □13	DQ27 □49
DQ3 □14	DQ19 □50
DQ11 □15	A3 □51
VCC □16	A10 □52
A0 □17	A4 □53
A7 □18	A11 □54
A1 □19	A5 □55
A8 □20	A12 □56
A2 □21	VCC □57
A9 □22	A13 □58
DQ12 □23	A6 □59
DQ4 □24	DQ20 □60
DQ13 □25	DQ28 □61
DQ5 □26	DQ21 □62
DQ14 □27	DQ29 □63
DQ6 □28	DQ22 □64
DQ15 □29	DQ30 □65
DQ7 □30	DQ23 □66
VSS □31	DQ31 □67
W \ □32	VSS □68
A15 □33	NC □69
A14 □34	NC □70
E2 \ □35	NC □71
E1 \ □36	NC □72

PD 1,2 = VSS
PD 3,4 = Open

PIN NAMES

A0-A17	Address Inputs
$\overline{E0}$ - $\overline{E3}$	Chip Enables
$\overline{W}$, $\overline{G}$	Write Enables
$\overline{G}$	Output Enable
DQ0-DQ31	Common Data Input/Output
VCC	Power (3.3V $\pm 10\%$)
VSS	Ground





ABSOLUTE MAXIMUM RATINGS*

Voltage on any pin relative to VSS	-0.5V to 4.6V
Operating Temperature TA (Ambient) Commercial	0°C to +70°C
Storage Temperature, Plastic	-55°C to +125°C
Power Dissipation	2.5 Watts
Output Current	20 mA

*Stress greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions greater than those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

Parameter	Sym	Min	Typ	Max	Units
Supply Voltage	VCC	3.0	3.3	3.6	V
Supply Voltage	VSS	0	0	0	V
Input High Voltage	VIH	2.2	--	VCC+0.3V	V
Input Low Voltage	VIL	-0.3	--	0.8	V

AC TEST CONDITIONS

Input Pulse Levels	VSS to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Levels	1.5V
Output Load	1TTL, CL = 30pF

(note: For TEHQZ, TGHQZ and TWLQZ, CL = 5pF)

DC ELECTRICAL CHARACTERISTICS

Parameter	Sym	Conditions	Min	Max 12-25	Units ns
Operating Power Supply Current	ICC1	$\overline{W}, \overline{E} = \text{VIL}, \text{II/O} = 0\text{mA}, \text{Min Cycle}$		800	mA
Standby (TTL) Power Supply Current	ICC2	$\overline{E} \geq \text{VIH}, \text{VIN} \leq \text{VIL} \text{ or } \text{VIN} \geq \text{VIH}$		240	mA
Full Standby Power Supply Current CMOS	ICC3	$\overline{E} \geq \text{VCC}-0.2\text{V}$ $\text{VIN} \geq \text{VCC}-0.2\text{V} \text{ or } \text{VIN} \leq 0.2\text{V}$		40	mA
Input Leakage Current	ILI	$\text{VIN} = 0\text{V to VCC}$	--	± 80	μA
Output Leakage Current	ILO	$\text{V I/O} = 0\text{V to VCC}$	--	± 20	μA
Output High Voltage	VOH	$\text{IOH} = -4.0\text{mA}$	2.4	--	V
Output Low Voltage	VOL	$\text{IOL} = 8.0\text{mA}$	--	0.4	V

TRUTH TABLE

$\overline{\text{E}}$	$\overline{\text{W}}$	$\overline{\text{G}}$	Mode	Output	Power
H	X	X	Standby	HIGH Z	ICC3
L	H	L	Read	DOUT	ICC1
L	L	X	Write	DIN	ICC1
L	H	H	Output Deselect	HIGH Z	ICC1

CAPACITANCE

(f=1.0MHz, VIN=VCC or VSS)

Parameter	Sym	Max	Unit
Address Lines	CI	60	pF
Data Lines	CD/Q	20	pF
Chip Enable Line	CC	20	pF
Write Control Line	CN	60	pF

These parameters are sampled, not 100% tested.



AC CHARACTERISTICS READ CYCLE

Parameter	Symbol		12ns		15ns		20ns		25ns		Units
	JEDEC	Alt	Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	TAVAV	TRC	12		15		20		25		ns
Address Access Time	TAVQV	TAA		12		15		20		25	ns
Chip Enable Access	TELQV	TACS		12		15		20		25	ns
Chip Enable to Output in Low Z (1)	TELQX	TCLZ	3		3		3		3		ns
Chip Disable to Output in High Z (1)	TEHQZ	TCHZ		6		7		9		9	ns
Output Hold from Address Change	TAVQX	TOH	3		3		3		3		ns
Output Enable to Output Valid	TGLQV	TOE		6		7		9		9	ns
Output Enable to Output in Low Z (1)	TGLQX	TOLZ	0		0		0		0		ns
Output Disable to Output in High Z (1)	TGHQZ	TOHZ		6		7		9		9	ns

Note 1: Parameter guaranteed, but not tested.

FIG. 2

READ CYCLE 1 - $\overline{W}$ HIGH, $\overline{G}$, $\overline{E}$ LOW

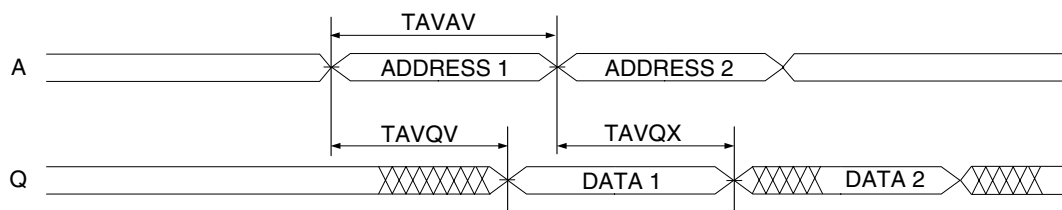
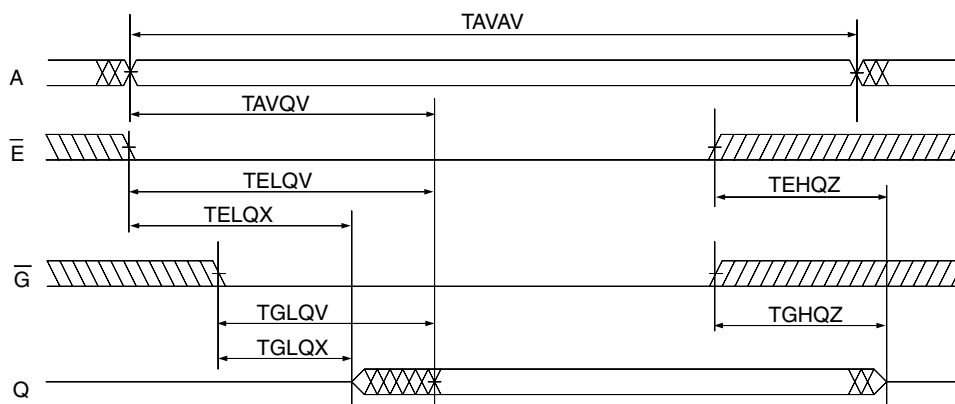


FIG. 3

READ CYCLE 2 - $\overline{W}$ HIGH



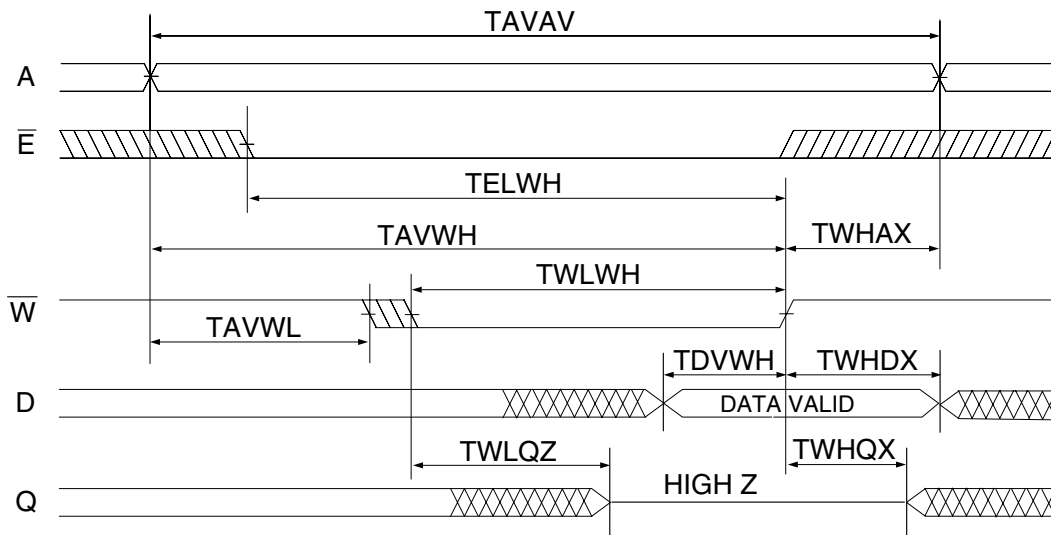
**AC CHARACTERISTICS WRITE CYCLE**

Parameter	Symbol		12ns		15ns		20ns		25ns		Units
	JEDEC	Alt.	Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	TAVAV	TWC	12		15		20		25		ns
Chip Enable to End of Write	TELWH	TCW	8		9		10		10		ns
	TWLEH	TCW	8		9		10		10		ns
Address Setup Time	TAVWL	TAS	0		0		0		0		ns
	TAVEL	TAS	0		0		0		0		ns
Address Valid to End of Write	TAVWH	TAW	8		9		10		10		ns
	TAVEH	TAW	8		9		10		10		ns
Write Pulse Width	TWLWH	TWP	8		9		10		10		ns
	TELEH	TWP	8		9		10		10		ns
Write Recovery Time	TWHAX	TWR	0		0		0		0		ns
	TEHAX	TWR	0		0		0		0		ns
Data Hold Time	TWHDX	TDH	3		3		3		3		ns
	TEHDX	TDH	3		3		3		3		ns
Write to Output in High Z (1)	TWLQZ	TWHZ	0	6	0	7	0	9	0	9	ns
Data to Write Time	TDVWH	TDW	6		7		8		8		ns
	TDVEH	TDW	6		7		8		8		ns
Output Active from End of Write (1)	TWHQX	TWLZ	3		3		3		3		ns

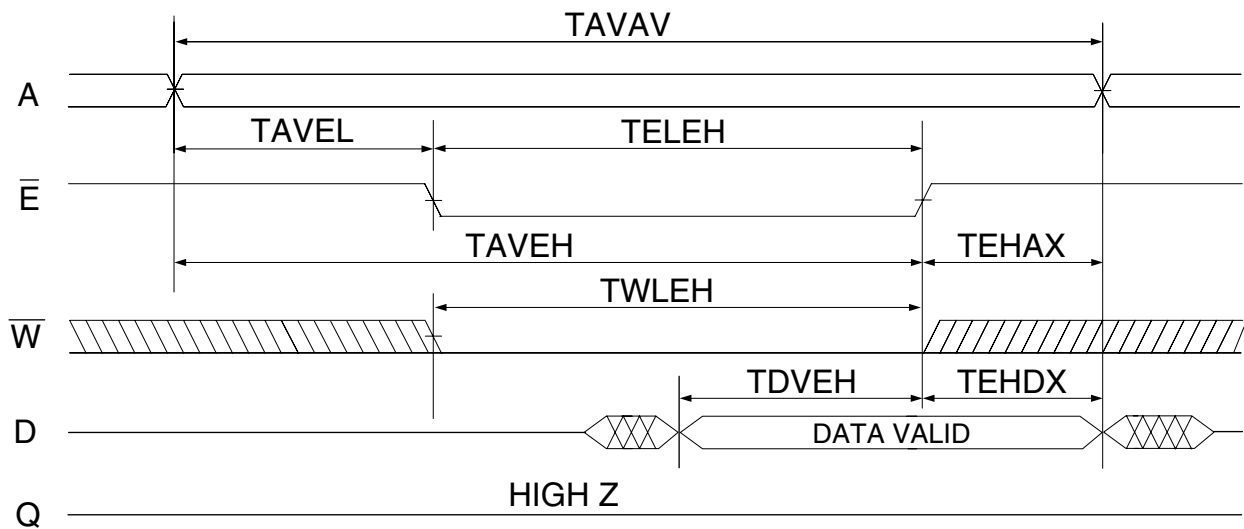
Note 1: Parameter guaranteed, but not tested.



WRITE CYCLE 1 - $\overline{W}$ CONTROLLED



WRITE CYCLE 2 - $\overline{E}$ CONTROLLED





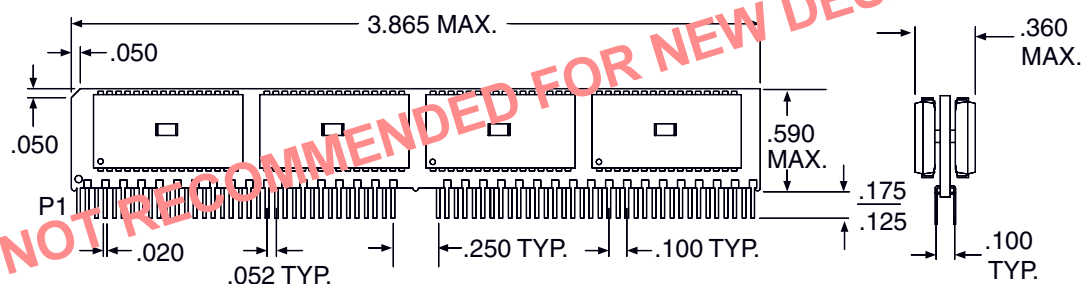
ORDERING INFORMATION

Part Number	Speed (ns)	Package No.
EDI8F32259V12MNC	12	176
EDI8F32259V15MNC	15	176
EDI8F32259V20MNC	20	176
EDI8F32259V25MNC	25	176
EDI8F32259V12MMC	12	354
EDI8F32259V15MMC	15	354
EDI8F32259V20MMC	20	354
EDI8F32259V25MMC	25	354
EDI8F32259V12MZC	12	175
EDI8F32259V15MZC	15	175
EDI8F32259V20MZC	20	175
EDI8F32259V25MZC	25	175

Note: For Gold SIMM, Change from EDI8F to EDI8G.

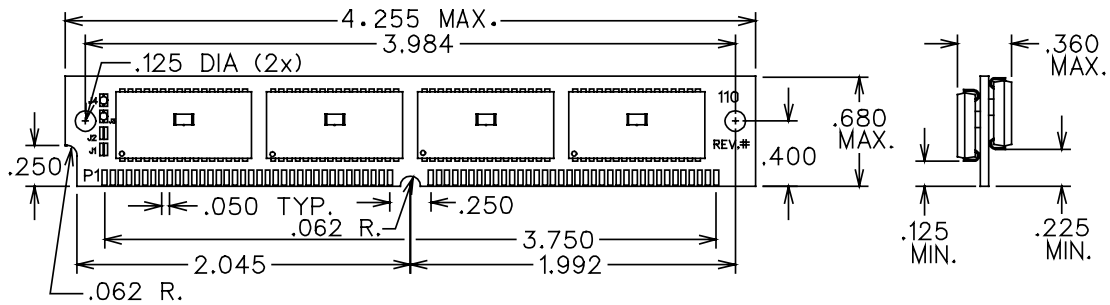
PACKAGE DESCRIPTION

PACKAGE NO. 175: 72 PIN ZIP

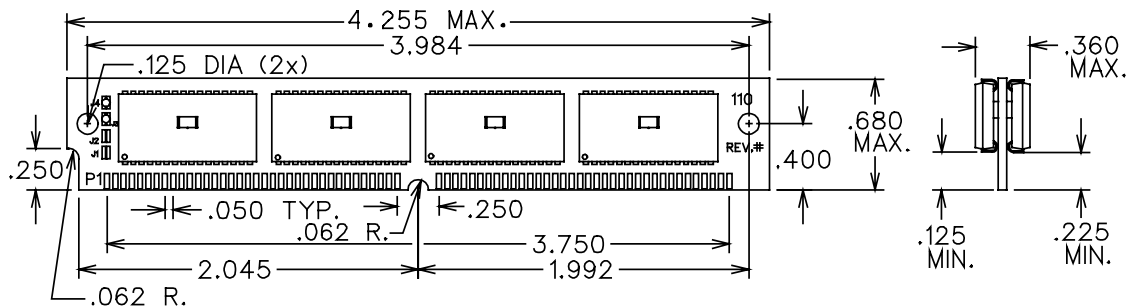




PACKAGE NO. 176: 72 PIN SIMM ANGLED



PACKAGE NO. 354: 72 PIN SIMM STRAIGHT



ALL DIMENSIONS ARE IN INCHES

DATASHEET APPROVALS

EDI PART NO. _____ ECO# _____
NEW REV _____ DATE _____

APPROVAL: **INITIAL** **DATE** **CORRECTION ON PAGES**

~~JUAN GUZMAN~~ L.K. _____ _____ _____

~~MUKESH TRIVEDI~~ M.A. _____ _____ _____

PAUL MARIEN _____ _____ _____

LARRY WINROTH _____ _____ _____

DAVE KELLY _____ _____ _____

MARK DOWNEY _____ _____ _____

DAVE HARRISON _____ _____ _____

TONY LEE _____ _____ _____

BOB KHEDERIAN _____ _____ _____

LUIS ESTELLA _____ _____ _____

WILL THIS DATASHEET GO ON THE WEB? YES NO LINE: _____

IS THIS A NEW DATASHEET? FAMILY: _____

WILL THIS DATASHEET REPLACE AN EXISTING
DATASHEET THAT'S ALREADY ON THE WEB? PROD.TYPE: _____

IF YES, WHAT DATASHEET IS IT REPLACING? ORG: _____

WHAT SECTION SHOULD THIS DATASHEET BE
PLACED IN ON THE WEB? DENSITY: _____

AFTER REVIEWING OR MAKING CORRECTIONS ON THE DATASHEET (S)
**PLEASE SIGN-OFF ON THIS SHEET AND ,MAKE YOUR CORRECTIONS –ON
THE ORIGINAL COPY(S).** SPEED: _____

AFTER REVIEWING THE DATA SHEET, TEST ENGINEERING WILL COMPLETE THE SECTION BELOW. PKG: _____

TEST PROGRAM CHANGE REQUIRED:
YES: _____ NO _____ DATE: _____

TEST ENGINEER SIGNATURE _____

IF YES, DO NOT RELEASE DATA SHEET UNTIL TEST PROGRAM CHANGE IS COMPLETED.

TEST PROGRAM CHANGE COMPLETION DATE: _____

TEST PROGRAM NAME AND REVISION _____

TEST ENGINEER SIGNATURE _____